2x512Kx8 DUALITHIC™ SRAM

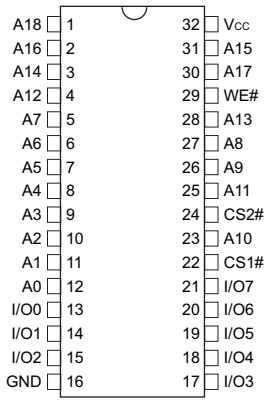
FEATURES

- Access Times 70, 85, 100ns
- Evolutionary, Corner Power/Ground Pinout
- Packaging:
  - 32 pin, Hermetic Ceramic DIP (Package 300)
- Organized as two banks of 512Kx8
- Commercial, Industrial and Military Temperature Ranges
- 5 Volt Power Supply
- Low Power CMOS
- TTL Compatible Inputs and Outputs
- Output Enable Internally tied to GND.

* This product is under development, is not qualified or characterized and is subject to change without notice.

Pin Configuration FOR WS1M8-XCX

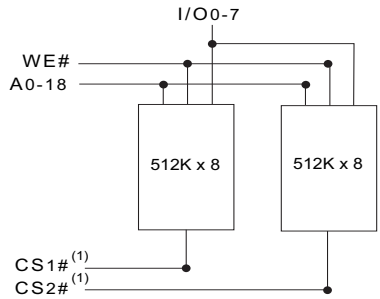
32 DIP
Top View



Pin Description

A0-18	Address Inputs
I/O0-7	Data Input/Output
CS1-2#	Chip Selects
WE#	Write Enable
VCC	+5.0V Power Supply
GND	Ground

Block Diagram



NOTE:
1. CS1# and CS2# are used to select the lower and upper 512Kx8 of the device. CS1# and CS2# must not be enabled at the same time.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T_A	-55	+125	°C
Storage Temperature	T_{STG}	-65	+150	°C
Signal Voltage Relative to GND	V_G	-0.5	V_{CC}+0.5	V
Junction Temperature	T_J		150	°C
Supply Voltage	V_{CC}	-0.5	7.0	V

TRUTH TABLE

CS#	WE#	Mode	Data I/O	Power
H	X	Standby	High Z	Standby
L	H	Read	Data Out	Active
L	L	Write	Data In	Active

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}	4.5	5.5	V
Input High Voltage	V_{IH}	2.2	V_{CC} + 0.3	V
Input Low Voltage	V_{IL}	-0.3	+0.8	V
Opertating Temp. (MIL)	T_A	-55	+125	°C

CAPACITANCE

T_A = +25°C

Parameter	Symbol	Conditions	Max	Unit
Input capacitance	C_{IN}	V_{IN} = 0V, f = 1.0 MHz	28	pF
Output capacitance	C_{OUT}	V_{OUT} = 0V, f = 1.0 MHz	28	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

V_{CC} = 5.0V, V_{SS} = 0V, -55°C ≤ T_A ≤ +125°C

Parameter	Sym	Conditions	Min	Max	Units
Input Leakage Current	I_{LI}	V_{CC} = 5.5, V_{IN} = GND to V_{CC}		10	µA
Output Leakage Current	I_{LO}[1]	CS# = V_{IH}, V_{OUT} = GND to V_{CC}		10	µA
Operating Supply Current	I_{CC}[1]	CS# = V_{IL}, f = 5MHz, V_{CC} = 5.5		55	mA
Standby Current	I_{SB}[1]	CS# = V_{IH}, f = 5MHz, V_{CC} = 5.5		2	mA
Output Low Voltage	V_{OL}	I_{OL} = 2.1mA		0.4	V
Output High Voltage	V_{OH}	I_{OH} = -1.0mA	2.4		V

NOTE: DC test conditions: V_{IH} = V_{CC} -0.3V, V_{IL} = 0.3V

1. OE# is internally tied to GND.

DATA RETENTION CHARACTERISTICS

-55°C ≤ T_A ≤ +125°C

Characteristic	Sym	Conditions	Min	Typ	Max	Units
Data Retention Supply Voltage	V_{DR}	CS# ≥ V_{CC} -0.2V	2.0		5.5	V
Data Retention Current	I_{CCDR1}	V_{CC} = 3V		150	800*	µA

* Also available in Low Power version. Please call factory for informaion.

AC CHARACTERISTICS

V_{CC} = 5.0V, GND = 0V, -55°C ≤ T_A ≤ +125°C

Parameter Read Cycle	Symbol	-70		-85		-100		Units
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	t_{RC}	70		85		100		ns
Address Access Time	t_{AA}		70		85		100	ns
Output Hold from Address Change	t_{OH}	0		0		0		ns
Chip Select Access Time	t_{ACS}		70		85		100	ns
Chip Select to Output in Low Z	t_{CLZ}[1]	5		5		5		ns
Chip Disable to Output in High Z	t_{CHZ}[1]		25		25		25	ns

1. This parameter is guaranteed by design but not tested.

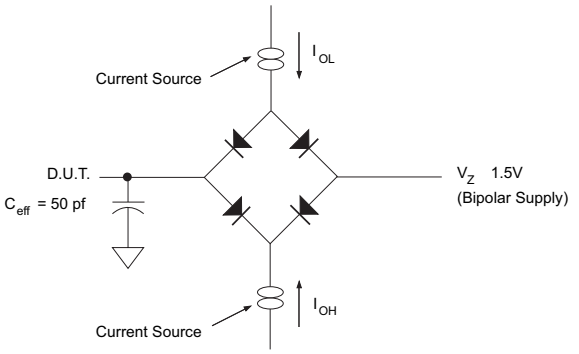
AC CHARACTERISTICS

V_{CC} = 5.0V, GND = 0V, -55°C ≤ T_A ≤ +125°C

Parameter Write Cycle	Symbol	-70		-85		-100		Units
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	t_{WC}	70		85		100		ns
Chip Select to End of Write	t_{CW}	60		75		80		ns
Address Valid to End of Write	t_{AW}	60		75		80		ns
Data Valid to End of Write	t_{DW}	30		30		40		ns
Write Pulse Width	t_{WP}	50		50		60		ns
Address Setup Time	t_{AS}	0		0		0		ns
Address Hold Time	t_{AH}	5		5		5		ns
Output Active from End of Write	t_{OW}[1]	5		5		5		ns
Write Enable to Output in High Z	t_{WHZ}[1]		25		25		35	ns
Data Hold Time	t_{DH}	0		0		0		ns

1. This parameter is guaranteed by design but not tested.

AC TEST CIRCUIT

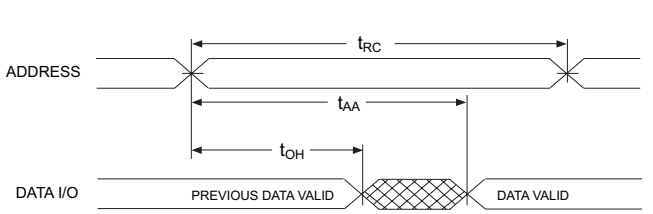


AC Test Conditions

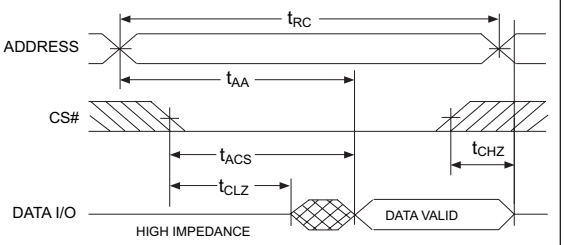
Parameter	Typ	Unit
Input Pulse Levels	V_{IL} = 0, V_{IH} = 3.0	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

Notes:
V_Z is programmable from -2V to +7V.
I_{OL} & I_{OH} programmable from 0 to 16mA.
Tester Impedance Z0 = 75Ω.
V_Z is typically the midpoint of V_{OH} and V_{OL}.
I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.
ATE tester includes jig capacitance.

TIMING WAVEFORM – READ CYCLE



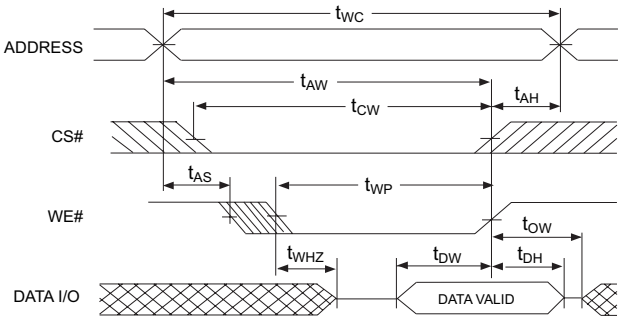
READ CYCLE 1 (CS# = V_{IL}, WE# = V_{IH})



READ CYCLE 2 (WE# = V_{IH})

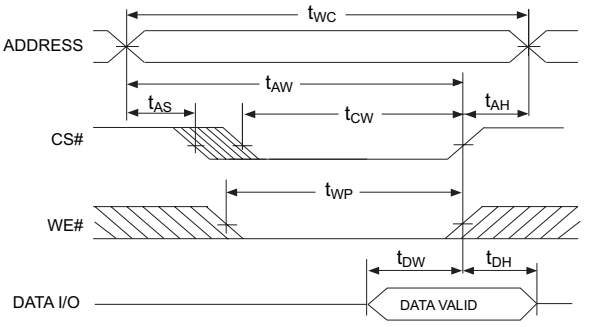
NOTE: OE# is internally tied to GND.

WRITE CYCLE – WE# CONTROLLED



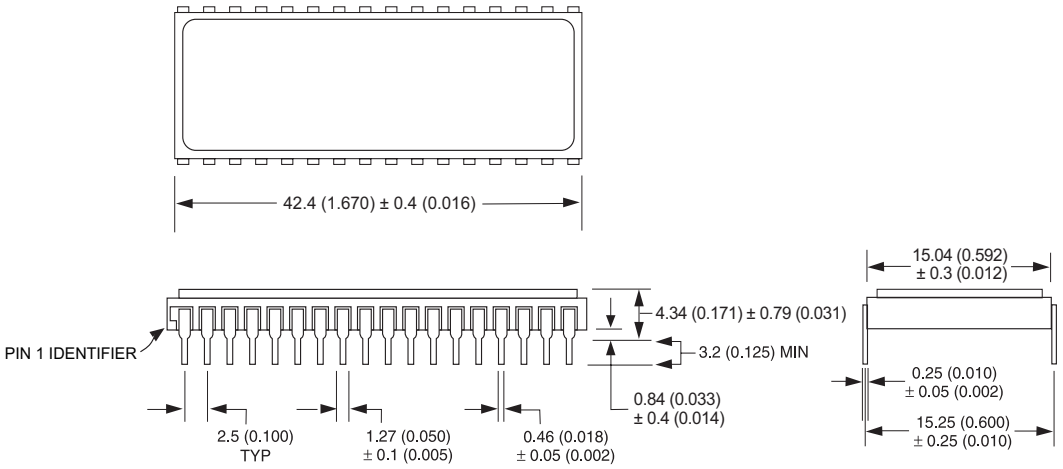
WRITE CYCLE 1, WE# CONTROLLED

WRITE CYCLE – CS# CONTROLLED



WRITE CYCLE 2, CS# CONTROLLED

PACKAGE 300: 32 PIN, CERAMIC DIP, SINGLE CAVITY SIDE BRAZED



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

ORDERING INFORMATION

W S 1M8 - XXX C X X

LEAD FINISH:
Blank = Gold plated leads
A = Solder dip leads

DEVICE GRADE:
M = Military Screened -55°C to +125°C
I = Industrial -40°C to +85°C
C = Commercial 0°C to +70°C

PACKAGE:
C = Ceramic 0.600" DIP (Package 300)

ACCESS TIME (ns)

ORGANIZATION, two banks of 512K x 8

SRAM

WHITE ELECTRONIC DESIGNS CORP.